

Di Wu

List of Publications by Year in descending order

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papers

6,213
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94269

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195
docs citations

195
times ranked

8274
citing authors

#	ARTICLE	IF	CITATIONS
1	Out-of-Plane Piezoelectricity and Ferroelectricity in Layered In_2Se_3 Nanoflakes. Nano Letters, 2017, 17, 5508-5513.	4.5	567
2	Ferroelectric-field-effect-enhanced electroresistance in metal/ferroelectric/semiconductor tunnel junctions. Nature Materials, 2013, 12, 617-621.	13.3	554
3	Freestanding crystalline oxide perovskites down to the monolayer limit. Nature, 2019, 570, 87-90.	13.7	398
4	Sequence of Events for the Formation of Titanate Nanotubes, Nanofibers, Nanowires, and Nanobelts. Chemistry of Materials, 2006, 18, 547-553.	3.2	247
5	Ultrathin ZnO coating for improved electrochemical performance of $\text{LiNi}_0.5\text{Co}_0.2\text{Mn}_0.3\text{O}_2$ cathode material. Journal of Power Sources, 2014, 266, 433-439.	4.0	212
6	Ferroelectric Tunnel Junctions: Modulations on the Potential Barrier. Advanced Materials, 2020, 32, e1904123.	11.1	179
7	Giant tunnelling electroresistance in metal/ferroelectric/semiconductor tunnel junctions by engineering the Schottky barrier. Nature Communications, 2017, 8, 15217.	5.8	165
8	Self-consistent determination of spin Hall angle and spin diffusion length in Pt and Pd: The role of the interface spin loss. Science Advances, 2018, 4, eaat1670.	4.7	157
9	Ferroelectric properties of $\text{Bi}_{3.25}\text{La}_{0.75}\text{Ti}_3\text{O}_{12}$ thin films prepared by chemical solution deposition. Journal of Applied Physics, 2000, 88, 5941-5945.	1.1	141
10	Imaging quantum spin Hall edges in monolayer WTe_2 . Science Advances, 2019, 5, eaat8799.	4.7	113
11	Thickness-Dependent Dielectric Constant of Few-Layer In_2Se_3 Nanoflakes. Nano Letters, 2015, 15, 8136-8140.	4.5	99
12	Uncovering edge states and electrical inhomogeneity in MoS_2 field-effect transistors. Proceedings of the National Academy of Sciences of the United States of America, 2016, 113, 8583-8588.	3.3	94
13	Processing- and composition-dependent characteristics of chemical solution deposited $\text{Bi}_{4-x}\text{La}_x\text{Ti}_3\text{O}_{12}$ thin films. Journal of Materials Research, 2001, 16, 1325-1332.	1.2	88
14	Fabrication and electrical properties of sol-gel derived BaTiO_3 films with metallic LaNiO_3 electrode. Applied Physics Letters, 1997, 70, 1616-1618.	1.5	87
15	Excellent resistive switching properties of atomic layer-deposited $\text{Al}_2\text{O}_3/\text{HfO}_2/\text{Al}_2\text{O}_3$ trilayer structures for non-volatile memory applications. Nanoscale Research Letters, 2015, 10, 135.	3.1	84
16	Ultrafast spin current generated from an antiferromagnet. Nature Physics, 2021, 17, 388-394.	6.5	81
17	Mechanism of Polarization Fatigue in BiFeO_3 . ACS Nano, 2012, 6, 8997-9004.	7.3	71
18	Mesoscale Imperfections in MoS_2 Atomic Layers Grown by a Vapor Transport Technique. Nano Letters, 2014, 14, 4682-4686.	4.5	67

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19	Dielectric characterization of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films. Applied Physics Letters, 2004, 84, 4505-4507.	1.5	65
20	Bipolar Resistive Switching Characteristics of HfO ₂ /TiO ₂ /HfO ₂ Trilayer-Structure RRAM Devices on Pt and TiN-Coated Substrates Fabricated by Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 393.	3.1	64
21	Characteristics of LaAlO ₃ gate dielectrics on Si grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2003, 83, 3540-3542.	1.5	61
22	Magnetic and transport properties of (Mn, Co)-codoped ZnO films prepared by radio-frequency magnetron cosputtering. Journal of Applied Physics, 2005, 98, 053908.	1.1	60
23	Experimental Observation of the Gate-Controlled Reversal of the Anomalous Hall Effect in the Intrinsic Magnetic Topological Insulator MnBi ₂ Te ₄ Device. Nano Letters, 2020, 20, 709-714.	4.5	60
24	Co-doped titanate nanotubes. Applied Physics Letters, 2005, 87, 112501.	1.5	59
25	A high-throughput stereo-imaging system for quantifying rape leaf traits during the seedling stage. Plant Methods, 2017, 13, 7.	1.9	59
26	Photovoltaic property of BiFeO ₃ thin films with 109Å° domains. Applied Physics Letters, 2011, 99, .	1.5	56
27	Structure and electrical properties of Bi _{3.15} Nd _{0.85} Ti ₃ O ₁₂ ferroelectric thin films. Journal of Applied Physics, 2004, 95, 4275-4281.	1.1	55
28	Thickness-dependent metal-insulator transition in epitaxial SrRuO ₃ ultrathin films. Journal of Applied Physics, 2015, 117, .	1.1	54
29	Magnetic Ordering and Structural Phase Transitions in a Strained Ultrathin SrRuO_3 Perovskite. Physical Review Letters, 2012, 109, 157003.	2.9	51
30	Enhanced ferromagnetism at the rhombohedral-tetragonal phase boundary in Pr and Mn co-substituted powders. Solid State Communications, 2010, 150, 2081-2084.	0.9	48
31	Memristive behaviors in Pt/BaTiO ₃ /Nb:SrTiO ₃ ferroelectric tunnel junctions. Applied Physics Letters, 2014, 105, .	1.5	47
32	Synaptic Plasticity and Learning Behaviors Mimicked in Single Inorganic Synapses of Pt/HfOx/ZnOx/TiN Memristive System. Nanoscale Research Letters, 2017, 12, 65.	3.1	46
33	Mechanical switching of ferroelectric polarization in ultrathin BaTiO ₃ films: The effects of epitaxial strain. Applied Physics Letters, 2014, 104, .	1.5	45
34	Fatigue study of metalorganic-decomposition-derived SrBi ₂ Ta ₂ O ₉ thin films: The effect of partial switching. Applied Physics Letters, 2000, 76, 2208-2210.	1.5	43
35	Electron mobility determination of efficient phosphorescent iridium complexes with tetraphenylimidodiphosphinate ligand via transient electroluminescence method. Applied Physics Letters, 2012, 100, 073303.	1.5	40
36	Photocatalytic activity and photocorrosion of atomic layer deposited ZnO ultrathin films for the degradation of methylene blue. Nanotechnology, 2015, 26, 024002.	1.3	40

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37	Giant magnetoresistance in transition-metal-doped ZnO films. <i>Applied Physics Letters</i> , 2006, 88, 252110.	1.5	39
38	Atomic layer deposition of ZnO/TiO ₂ nanolaminates as ultra-long life anode material for lithium-ion batteries. <i>Scientific Reports</i> , 2019, 9, 11526.	1.6	38
39	Spin-Filtering Ferroelectric Tunnel Junctions as Multiferroic Synapses for Neuromorphic Computing. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 56300-56309.	4.0	37
40	Fabrication and characterization of La-doped HfO ₂ gate dielectrics by metal-organic chemical vapor deposition. <i>Applied Surface Science</i> , 2010, 256, 2496-2499.	3.1	35
41	Atomic Layer Deposited Oxide-Based Nanocomposite Structures with Embedded CoPt Nanocrystals for Resistive Random Access Memory Applications. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 6634-6643.	4.0	33
42	Characterization of metalorganic decomposition-derived SrBi ₂ Ta ₂ O ₉ thin films with different thicknesses. <i>Journal of Applied Physics</i> , 2000, 87, 1795-1800.	1.1	32
43	Polarization fatigue of Pr and Mn co-substituted BiFeO ₃ thin films. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	32
44	Self-catalysis by aminosilanes and strong surface oxidation by O ₂ plasma in plasma-enhanced atomic layer deposition of high-quality SiO ₂ . <i>Chemical Communications</i> , 2015, 51, 1341-1344.	2.2	32
45	Observation of spin-orbit magnetoresistance in metallic thin films on magnetic insulators. <i>Science Advances</i> , 2018, 4, eaao3318.	4.7	32
46	Temperature-dependent tunneling electroresistance in Pt/BaTiO ₃ /SrRuO ₃ ferroelectric tunnel junctions. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	31
47	Multiferroic properties of (Bi _{1-x} Pr _x)(Fe _{0.95} Mn _{0.05})O ₃ thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011, 176, 990-995.	1.7	30
48	Comparison of chemical stability and corrosion resistance of group IV metal oxide films formed by thermal and plasma-enhanced atomic layer deposition. <i>Scientific Reports</i> , 2019, 9, 10438.	1.6	30
49	Preparation of (Ba _{0.5} Sr _{0.5})TiO ₃ thin films by sol-gel method with rapid thermal annealing. <i>Applied Surface Science</i> , 2000, 165, 309-314.	3.1	28
50	Different growth behavior of SrBi ₂ Ta ₂ O ₉ ferroelectric films under conventional and rapid annealing processing by metalorganic decomposition. <i>Journal of Crystal Growth</i> , 2002, 235, 394-400.	0.7	28
51	Optical properties of (Mn, Co) co-doped ZnO films prepared by dual-radio frequency magnetron sputtering. <i>Thin Solid Films</i> , 2006, 515, 2361-2365.	0.8	28
52	Preparation of (1-x)(Na _{0.5} Bi _{0.5})TiO ₃ -xSrTiO ₃ thin films by a sol-gel method for dielectric tunable applications. <i>Journal of Sol-Gel Science and Technology</i> , 2009, 49, 29-34.	1.1	28
53	Ferroelectric domain inversion and its stability in lithium niobate thin film on insulator with different thicknesses. <i>AIP Advances</i> , 2016, 6, .	0.6	28
54	Electrical properties of chemical-solution-derived Bi _{3.54} Nd _{0.46} Ti ₃ O ₁₂ ferroelectric thin films. <i>Journal of Applied Physics</i> , 2003, 94, 7376-7378.	1.1	26

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55	Temperature-dependent leakage current characteristics of Pr and Mn cosubstituted BiFeO ₃ thin films. Applied Physics Letters, 2010, 96, 202904.	1.5	26
56	Polarization switching in quasiplanar BiFeO ₃ capacitors. Applied Physics Letters, 2010, 97, .	1.5	26
57	Design of Nanoporous to Compact Interface via Atomic/Molecular Layer Deposition Enabling a Long-Life Silicon Anode. Advanced Functional Materials, 2022, 32, 2109682.	7.8	26
58	The metallic interface between insulating NdGaO ₃ and SrTiO ₃ perovskites. Applied Physics Letters, 2013, 103, 201602.	1.5	25
59	Tuning Electron-Conduction and Spin Transport in Magnetic Iron Oxide Nanoparticle Assemblies via Tetrathiafulvalene-Fused Ligands. ACS Nano, 2015, 9, 12205-12213.	7.3	25
60	Atomic-scale fatigue mechanism of ferroelectric tunnel junctions. Science Advances, 2021, 7, eabh2716.	4.7	25
61	Effect of excess bismuth on the microstructures and electrical properties of strontium bismuth tantalate (SBT) thin films. Thin Solid Films, 2000, 375, 215-219.	0.8	24
62	Effects of processing on the characteristics of SrBi ₂ Ta ₂ O ₉ films prepared by metalorganic decomposition. Journal of Applied Physics, 2000, 88, 1035-1041.	1.1	24
63	Effects of the substitution of Pb for Ba in (Ba,Sr)TiO ₃ films on the temperature stability of the tunable properties. Applied Physics Letters, 2006, 88, 182909.	1.5	24
64	Growth characteristics of Ti-based fumaric acid hybrid thin films by molecular layer deposition. Dalton Transactions, 2015, 44, 14782-14792.	1.6	24
65	A comparative study of growth and properties of atomic layer deposited transparent conductive oxide of Al doped ZnO films from different Al precursors. Thin Solid Films, 2018, 646, 126-131.	0.8	24
66	Effect of uniaxial stress on the polarization of SrBi ₂ Ta ₂ O ₉ thin films. Applied Physics Letters, 2000, 76, 3103-3105.	1.5	23
67	Tuning the polarization state of light via time retardation with a microstructured surface. Physical Review B, 2013, 88, .	1.1	22
68	Optimization of oxygen vacancy concentration in HfO ₂ /HfO _x bilayer-structured ultrathin memristors by atomic layer deposition and their biological synaptic behavior. Journal of Materials Chemistry C, 2020, 8, 12478-12484.	2.7	22
69	Fabrication and electrical properties of sol-gel derived (BaSr)TiO ₃ thin films with metallic LaNiO ₃ electrode. Thin Solid Films, 1998, 336, 172-175.	0.8	21
70	ZnO/ZnS Core-Shell Nanowires Arrays on Ni Foam Prepared by Atomic Layer Deposition for High Performance Supercapacitors. Journal of the Electrochemical Society, 2017, 164, A3493-A3498.	1.3	21
71	TiO _x N _y Modified TiO ₂ Powders Prepared by Plasma Enhanced Atomic Layer Deposition for Highly Visible Light Photocatalysis. Scientific Reports, 2018, 8, 12131.	1.6	21
72	Synaptic functions and a memristive mechanism on Pt/AlO ₃ /HfO ₃ /TiN bilayer-structure memristors. Journal Physics D: Applied Physics, 2020, 53, 035302.	1.3	20

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73	Growth and characterization of Al ₂ O ₃ gate dielectric films by low-pressure metalorganic chemical vapor deposition. <i>Microelectronic Engineering</i> , 2003, 66, 842-848.	1.1	19
74	Nonvolatile memory capacitors based on Al ₂ O ₃ tunneling and HfO ₂ blocking layers with charge storage in atomic-layer-deposited Pt nanocrystals. <i>Applied Surface Science</i> , 2014, 289, 332-337.	3.1	19
75	Improved memory functions in multiferroic tunnel junctions with a dielectric/ferroelectric composite barrier. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	19
76	Electroelastic Green's function of one-dimensional piezoelectric quasicrystals subjected to multi-physics loads. <i>Journal of Intelligent Material Systems and Structures</i> , 2017, 28, 1651-1661.	1.4	19
77	Biomimetic strain sensors based on patterned polydimethylsiloxane and Ir nanoparticles decorated multi-walled carbon nanotubes. <i>Sensors and Actuators A: Physical</i> , 2019, 289, 57-64.	2.0	19
78	Anomalous Hall effect in Co/Ni multilayers with perpendicular magnetic anisotropy. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	18
79	Atomic-Layer-Deposition Assisted Formation of Wafer-Scale Double-Layer Metal Nanoparticles with Tunable Nanogap for Surface-Enhanced Raman Scattering. <i>Scientific Reports</i> , 2017, 7, 5161.	1.6	18
80	Current-voltage characteristics of sol-gel derived SrZrO ₃ thin films for resistive memory applications. <i>Journal of Alloys and Compounds</i> , 2011, 509, 2050-2053.	2.8	17
81	Light-Enhanced Spin Diffusion in Hybrid Perovskite Thin Films and Single Crystals. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 3205-3213.	4.0	17
82	Transition of laser-induced terahertz spin currents from torque- to conduction-electron-mediated transport. <i>Physical Review B</i> , 2022, 105, .	1.1	17
83	Leakage current characteristics of Pt-Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ -Pt thin-film capacitors. <i>Journal of Applied Physics</i> , 2005, 97, 106110.	1.1	16
84	Strontium-modified lead zirconate titanate thin films for electrically tunable device applications. <i>Journal of Applied Physics</i> , 2006, 100, 036102.	1.1	16
85	Four-state non-volatile memory in a multiferroic spin filter tunnel junction. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	16
86	Tailoring Stress and Ion-Transport Kinetics via a Molecular Layer Deposition-Induced Artificial Solid Electrolyte Interphase for Durable Silicon Composite Anodes. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 32520-32530.	4.0	16
87	Synthesis, structure and physical properties of the one-dimensional chain complex of tetrathiafulvalene carboxylate. <i>Science in China Series B: Chemistry</i> , 2009, 52, 1596-1601.	0.8	15
88	Impact of the Al/Hf ratio on the electrical properties and band alignments of atomic-layer-deposited HfO ₂ /Al ₂ O ₃ on S-passivated GaAs substrates. <i>Semiconductor Science and Technology</i> , 2010, 25, 055012.	1.0	15
89	Strain effects on magnetic characteristics of ultrathin La _{0.7} Sr _{0.3} MnO ₃ in epitaxial La _{0.7} Sr _{0.3} MnO ₃ /BaTiO ₃ superlattices. <i>Journal of Applied Physics</i> , 2012, 112, 123919.	1.1	14
90	Enhancing magnetoresistance in tetrathiafulvalene carboxylate modified iron oxide nanoparticle assemblies. <i>Nanoscale</i> , 2016, 8, 12128-12133.	2.8	14

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91	Simulation of Biologic Synapse Through Organic-Inorganic Hybrid Memristors Using Novel Ti-Based Maleic Acid/TiO ₂ Ultrathin Films. IEEE Electron Device Letters, 2020, 41, 155-158.	2.2	14
92	Preparation and characterization of a flexible ferroelectric tunnel junction. Applied Physics Letters, 2020, 116, .	1.5	14
93	Electroresistance in metal/ferroelectric/semiconductor tunnel junctions based on a Hf _{0.5} Zr _{0.5} O ₂ barrier. Applied Physics Letters, 2021, 118, .	1.5	14
94	Ferroelectric properties of bilayer structured Pb(Zr _{0.52} Ti _{0.48})O ₃ /SrBi ₂ Ta ₂ O ₉ (PZT/SBT) thin films on Pt/TiO ₂ /SiO ₂ /Si substrates. Applied Surface Science, 2008, 254, 1583-1586.	3.1	13
95	Recent advances in spin transport in organic semiconductors. Science China: Physics, Mechanics and Astronomy, 2013, 56, 142-150.	2.0	13
96	Resistive switching in BiFeO ₃ -based heterostructures due to ferroelectric modulation on interface Schottky barriers. Journal of Materials Science: Materials in Electronics, 2014, 25, 3251-3256.	1.1	13
97	Electromechanical Response from LaAlO ₃ /SrTiO ₃ Heterostructures. ACS Applied Materials & Interfaces, 2015, 7, 10146-10151.	4.0	13
98	Giant Thermal Transport Tuning at a Metal/Ferroelectric Interface. Advanced Materials, 2022, 34, e2105778.	11.1	13
99	Characteristics of metal-ferroelectric-insulator-semiconductor structure using La-modified Bi ₄ Ti ₃ O ₁₂ as the ferroelectric layer. Microelectronic Engineering, 2003, 66, 773-778.	1.1	12
100	Low-temperature electrical characteristics of Bi _{3.15} Nd _{0.85} Ti ₃ O ₁₂ thin films. Applied Physics Letters, 2007, 90, 062902.	1.5	12
101	Outstanding memory characteristics with atomic layer deposited Ta ₂ O ₅ /Al ₂ O ₃ /TiO ₂ /Al ₂ O ₃ /Ta ₂ O ₅ nanocomposite structures as the charge trapping layer. Applied Surface Science, 2019, 467-468, 423-427.	3.1	12
102	Ferroelastic-Domain-Assisted Mechanical Switching of Ferroelectric Domains in Pb(Zr,Ti)O ₃ Thin Films. Advanced Electronic Materials, 2020, 6, 2000300.	2.6	12
103	Strain Control of Phase Transition and Exchange Bias in Flexible Heusler Alloy Thin Films. ACS Applied Materials & Interfaces, 2021, 13, 24285-24294.	4.0	12
104	Raman spectroscopy and x-ray diffraction study of PbTiO ₃ thin films prepared by sol-gel technique. Journal of Applied Physics, 1999, 85, 2146-2150.	1.1	11
105	Interfacial structure in epitaxial perovskite oxides on (001) Ge crystal. Applied Physics Letters, 2015, 106, .	1.5	11
106	Band structure engineering of van der Waals heterostructures using ferroelectric clamped sandwich structures. Physical Review B, 2021, 103, .	1.1	11
107	Raman spectroscopy and X-ray diffraction study of sol-gel derived (Pb _{1-x} Lax)Ti _{1-x} /4O ₃ thin films on Si substrates. Thin Solid Films, 1998, 322, 323-328.	0.8	10
108	Bipolar resistive switching based on SrTiO ₃ /YBa ₂ Cu ₃ O ₇ epi-layers. Journal Physics D: Applied Physics, 2013, 46, 035308.	1.3	10

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109	Stepwise mechanism and H ₂ O-assisted hydrolysis in atomic layer deposition of SiO ₂ without a catalyst. <i>Nanoscale Research Letters</i> , 2015, 10, 68.	3.1	10
110	Periodic magnetic domains in single-crystalline cobalt filament arrays. <i>Physical Review B</i> , 2016, 93, .	1.1	10
111	High-resolution characterization of multiferroic heterojunction using aberration-corrected scanning transmission electron microscopy. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	10
112	Growth Mechanism, Ambient Stability, and Charge Trapping Ability of Ti-Based Maleic Acid Hybrid Films by Molecular Layer Deposition. <i>Langmuir</i> , 2019, 35, 3020-3030.	1.6	10
113	Effects of applied electric field during postannealing on the tunable properties of (Ba,Sr)TiO ₃ thin films. <i>Applied Physics Letters</i> , 2005, 87, 052902.	1.5	9
114	Bell-mouthed single-crystalline tubular ZnO prepared by a soft solution method. <i>Materials Chemistry and Physics</i> , 2006, 96, 51-54.	2.0	9
115	Structural phase transition due to La substitution in Bi ₄ Ti ₃ O ₁₂ . <i>Phase Transitions</i> , 2009, 82, 146-155.	0.6	9
116	Positron annihilation studies on the behaviour of vacancies in LaAlO ₃ /SrTiO ₃ heterostructures. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 445305.	1.3	9
117	Ferroelectric modulation on resonant tunneling through perovskite double-barriers. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	9
118	Titanicene-derived TiO ₂ quantum dot@carbon encapsulated ZnO nanorod anodes for stable lithium storage. <i>Dalton Transactions</i> , 2020, 49, 10866-10873.	1.6	9
119	One-step facile preparation of zinc-based hydroquinone hybrid nanoporous thin films by molecular layer deposition. <i>Applied Physics Letters</i> , 2020, 117, 031601.	1.5	9
120	Room temperature aging behavior of thermally imprinted Pt/SrBi ₂ Ta ₂ O ₉ /Pt ferroelectric thin film capacitors. <i>Journal of Applied Physics</i> , 2001, 90, 4130-4133.	1.1	8
121	Bipolar resistive switching in BiFe _{0.95} Zn _{0.05} O ₃ films. <i>Chinese Physics B</i> , 2013, 22, 107702.	0.7	8
122	Monolayer FePt nanocrystal self-assembly embedded into atomic-layer-deposited Al ₂ O ₃ films for nonvolatile memory applications. <i>Journal of Alloys and Compounds</i> , 2014, 588, 103-107.	2.8	8
123	Effective anomalous Hall coefficient in an ultrathin Co layer sandwiched by Pt layers. <i>Journal of Applied Physics</i> , 2014, 115, .	1.1	8
124	Effects of γ -ray irradiation on ferroelectric properties of Pr and Mn co-substituted BiFeO ₃ thin films. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 045310.	1.3	8
125	Interfacial, Electrical, and Band Alignment Characteristics of HfO ₂ /Ge Stacks with In Situ-Formed SiO ₂ Interlayer by Plasma-Enhanced Atomic Layer Deposition. <i>Nanoscale Research Letters</i> , 2017, 12, 370.	3.1	8
126	Structure and electrical properties of SrBi ₂ Ta ₂ O ₉ thin films annealed in different atmosphere. <i>Materials Letters</i> , 2001, 49, 303-307.	1.3	7

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127	Role of interfacial diffusion in SrBi ₂ Ta ₂ O ₉ thin-film capacitors. Microelectronic Engineering, 2003, 66, 654-661.	1.1	7
128	Fatigue characteristics of Nd-substituted Bi ₄ Ti ₃ O ₁₂ ferroelectric thin films at elevated temperatures. Journal Physics D: Applied Physics, 2008, 41, 122003.	1.8	7
129	Flexoelectric-induced photovoltaic effects and tunable photocurrents in flexible LaFeO ₃ epitaxial heterostructures. Journal of Materiomics, 2022, 8, 281-287.	2.8	7
130	Effects of processing on all-optical poling characteristics of guest-host azo-dye polymer thin films. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 1114-1122.	0.8	6
131	Polarization offsets of compositionally graded Nd-substituted Bi ₄ Ti ₃ O ₁₂ ferroelectric thin films. Applied Physics Letters, 2008, 93, 062904.	1.5	6
132	Microstructures and impedance studies of Bi _{3.15} Nd _{0.85} Ti ₃ O ₁₂ thin films. Applied Physics A: Materials Science and Processing, 2009, 95, 517-521.	1.1	6
133	Chemical strain-dependent two-dimensional transport at $\text{AlO}_x/\text{Bi}_4\text{Ti}_3\text{O}_{12}$ interfaces		

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145	Characteristics of Gd _{2-x} La _x O ₃ high-k films by metal-organic chemical vapor deposition. <i>Microelectronic Engineering</i> , 2012, 94, 38-43.	1.1	4
146	TiAlO nanocrystal charge trapping memory cells fabricated by atomic layer deposition. <i>Thin Solid Films</i> , 2014, 563, 6-9.	0.8	4
147	Improved thermal stability and electrical properties of atomic layer deposited HfO ₂ /AlN high-k gate dielectric stacks on GaAs. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	4
148	Electrically tunable inverse spin Hall effect in SrIrO ₃ /Pb(Mg _{1/3} Nb _{2/3}) _{0.7} Ti _{0.3} O ₃ heterostructures through interface strain coupling. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	4
149	Stable pH sensitivity of LaAlO ₃ /SrTiO ₃ interfacial electronic gas. <i>Current Applied Physics</i> , 2022, 34, 55-58.	1.1	4
150	Characterization of SrBi ₂ Ta ₂ O ₉ films prepared by metalorganic decomposition using rapid thermal annealing. <i>Integrated Ferroelectrics</i> , 2001, 33, 253-259.	0.3	3
151	Characteristics of SrBi ₂ Ta ₂ O ₉ ferroelectric films in an in situ applied low electric field prepared by metalorganic decomposition. <i>Solid State Communications</i> , 2003, 125, 469-473.	0.9	3
152	Electrical properties of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ /LaAlO ₃ /Si structures for ferroelectric field effect transistor applications. <i>Journal Physics D: Applied Physics</i> , 2004, 37, 832-835.	1.3	3
153	SYNTHESIS AND CHARACTERIZATION OF FERROELECTRIC NANOCRYSTAL POWDERS OF SrBi ₂ Ta ₂ O ₉ BY A POLYMERIZABLE COMPLEX METHOD. <i>International Journal of Modern Physics B</i> , 2005, 19, 2514-2519.	1.0	3
154	Composition-dependent electrical characteristics and interface microstructures of solution-derived Nd-substituted Bi ₄ Ti ₃ O ₁₂ thin films on Pt electrodes. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 185412.	1.3	3
155	Spectroscopy of self-assembled one-dimensional atomic string: The role of step edge. <i>Applied Physics Letters</i> , 2013, 103, 081608.	1.5	3
156	Evaluation of the Structural Phase Transition in Multiferroic (Bi _{1-x} Pr _x)(Fe _{0.95} Mn _{0.05})O ₃ Thin Films by A Multi-Technique Approach Including Picosecond Laser Ultrasonics. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 736.	1.3	3
157	Thickness-dependent structural phase transition and self-intercalation of two-dimensional ferromagnetic chromium telluride thin films. <i>Applied Physics Letters</i> , 2022, 120, 261602.	1.5	3
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